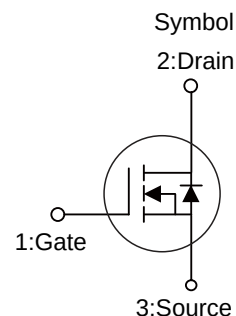


PRODUCT CHARACTERISTICS

V_{DSS}	600V
$R_{DS(ON)} Typ(@V_{GS}=10V)$	$1.8\ \Omega$
$Q_g@typ$	12.5nC
I_D	5A

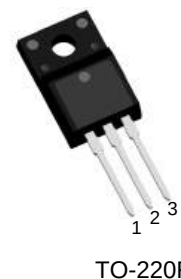


APPLICATIONS

- * Electronic lamp ballasts based on half bridge
- * Load Switching, Quick/Wireless Charge.
- * Motor Driving

FEATURE

- * Low Gate Charge
- * Pb-Free Lead Plating



ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT5N60F	TO-220F	50 pieces/Tube

ABSOLUTE MAXIMUM RATINGS($T_c = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	250	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current Continuous($@V_{GS}=10V, T_c=25^\circ\text{C}$)	I_D	5	A
Drain Current Continuous($@V_{GS}=10V, T_c=100^\circ\text{C}$)	I_D	3.1	A
Drain Current Pulsed	I_{DM}	20	A
Avalanche Energy *	E_{AS}	245	mJ
Power Dissipation	P_D	30	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Case	R_{thJC}	4.17	$^\circ\text{C/W}$

Note: * EAS condition: $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=10mH, R_g=25\ \Omega$

■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V _{DSS}	V _{GS} =0V,I _D =250μA	600	-	-	V
Drain to Source Leakage Current	I _{DSS}	V _{DS} =600V,V _{GS} =0V	-	-	1	μA
Gate to Source Forward Leakage	I _{GSS(F)}	V _{GS} =+30V,V _{DS} =0V	-	-	100	nA
Gate to Source Reverse Leakage	I _{GSS(R)}	V _{GS} =-30V ,V _{DS} =0V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	R _{DS(ON)}	V _{GS} =10V,I _D =2.5A	-	1.8	2.4	Ω
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} ,I _D =250μA	2	3.1	4	V
Dynamic characteristics						
Gate capacitance	R _g	V _{GS} =0V,V _{DS} =0V ,f=1.0MHz	-	3	-	Ω
Forward Transconductance	g _{fs}	V _{DS} =10V,I _D =2A	-	4.2	-	S
Input Capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V f=1.0MHz	-	638	-	pF
Output Capacitance	C _{oss}		-	50	-	pF
Reverse Transfer Capacitance	C _{rss}		-	7.3	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	t _{d(ON)}	V _{GS} =10V, V _{DS} =300V, I _D =5 A ,R _G =10Ω	-	14	-	ns
Rise Time	t _r		-	15	-	ns
Turn-off Delay Time	t _{d(OFF)}		-	34	-	ns
Fall Time	t _f		-	13	-	ns
Total Gate Charge	Q _g	I _D =5 A, V _{DS} =300V V _{GS} =10V	-	12.5	-	nC
Gate to Source Charge	Q _{gs}		-	2.6	-	nC
Gate to Drain("Miller") Charge	Q _{gd}		-	5.5	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I _s		-	-	5	A
Maximum Pulsed Current(Body Diode)	I _{SM}		-	-	20	A
Diode Forward Voltage	V _{SD}	I _{SD} =1A, V _{GS} =0V	-	0.74	1.2	V
Reverse Recovery Time	t _{rr}	I _{SD} =10A, T _j =25℃	-	250	-	ns
Reverse Recovery Charge	Q _{rr}	di /dt=100A/μs	-	1000	-	nC

■ TYPICAL CHARACTERISTICS

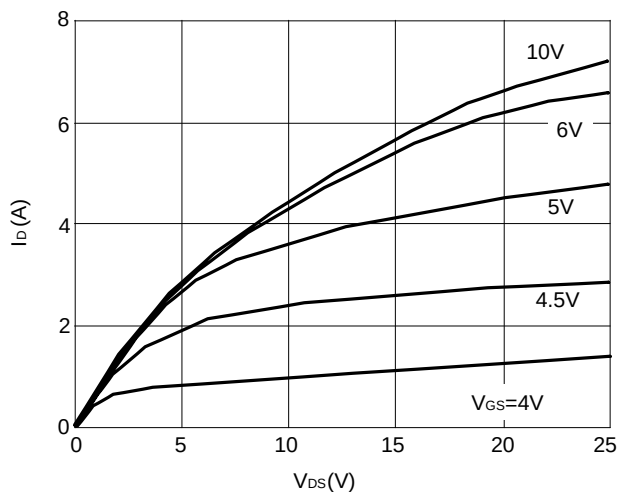


Figure 1: Output Characteristics

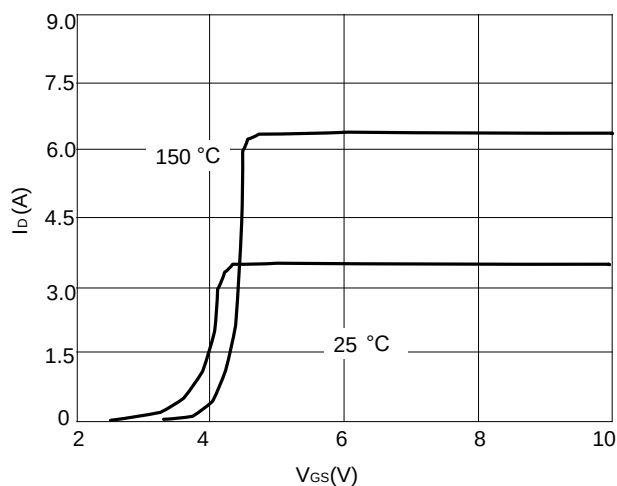


Figure 2: Typical Transfer Characteristics

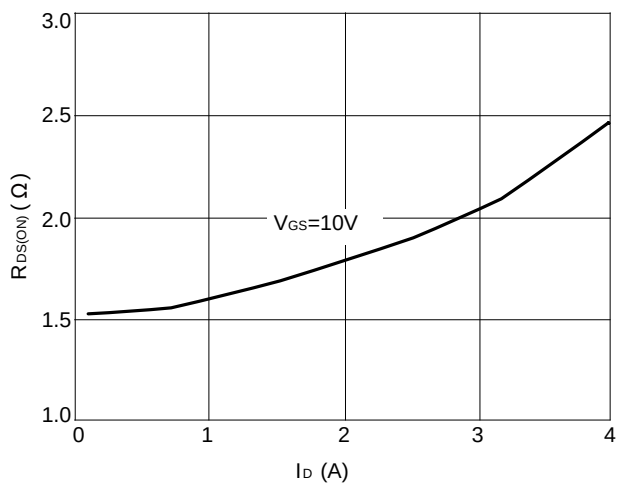


Figure 3: On-Resistance vs. Drain Current

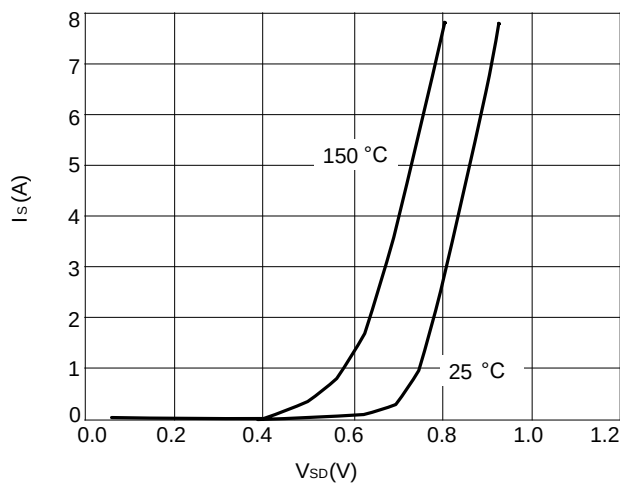


Figure 4: Body Diode Characteristics

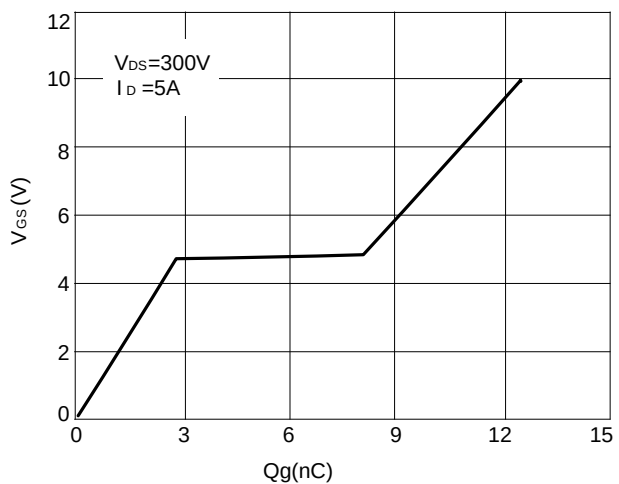


Figure 5: Gate Charge Characteristics

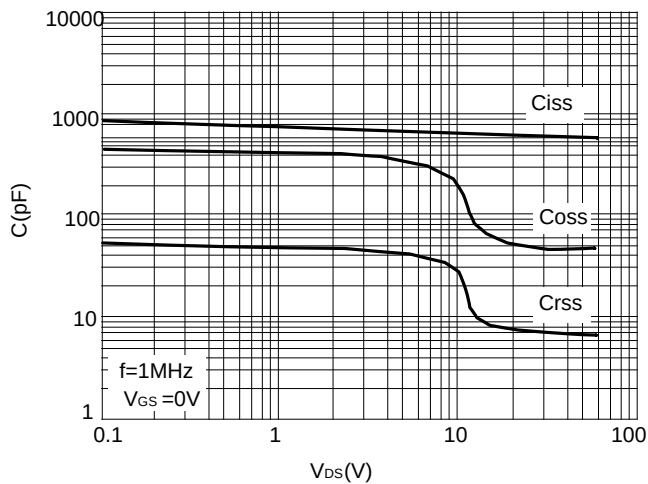


Figure 6: Capacitance Characteristics

■ TYPICAL CHARACTERISTICS(Cont.)

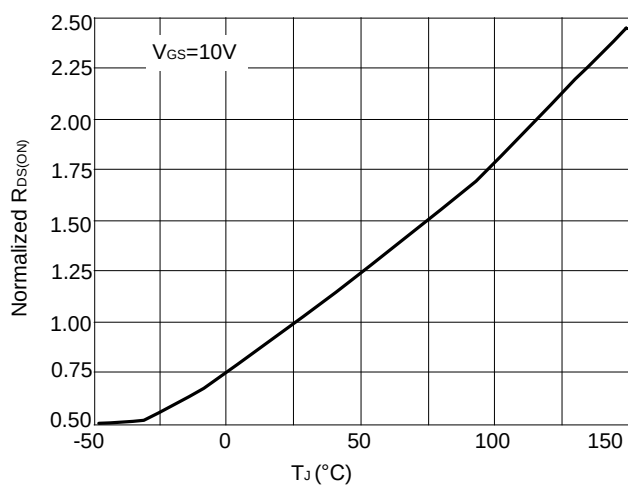


Figure 7: Normalized on-Resistance vs. Junction Temperature

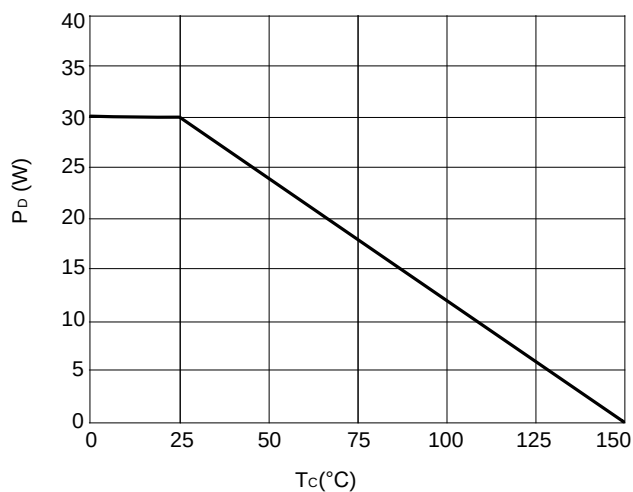


Figure 8: Power De-rating

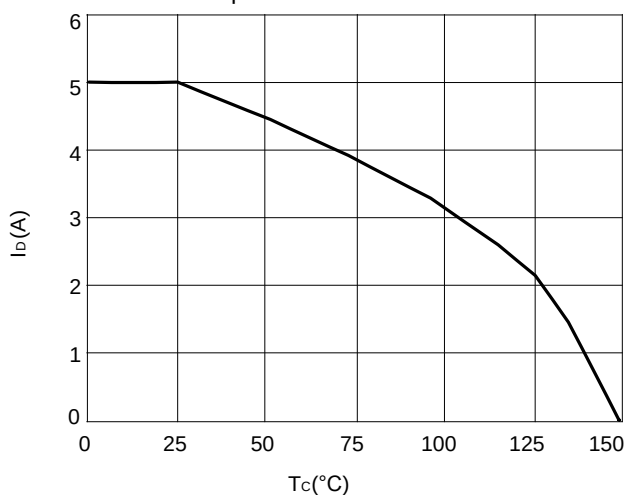


Figure 9: Current De-rating

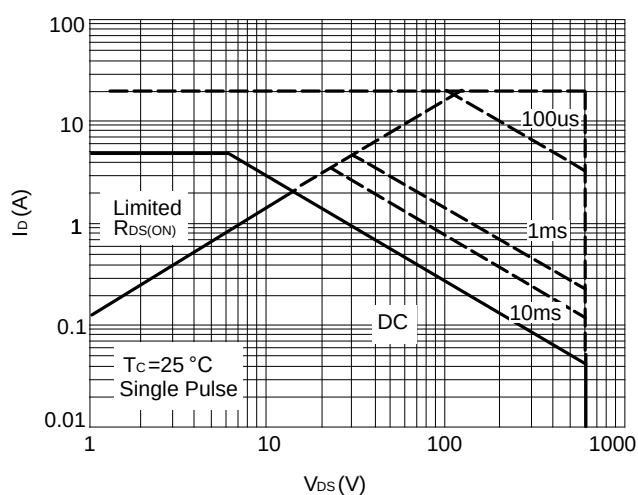


Figure 10: Maximum Safe Operating Area

■ TO-220F PACKAGE OUTLINE DIMENSIONS

